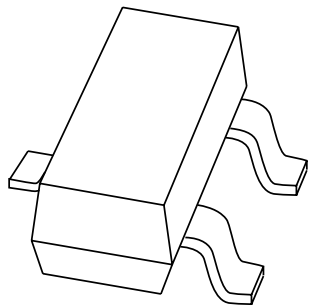


# DATA SHEET



## **BAP1321-04** Silicon PIN diode

Product specification

2001 Apr 17

Silicon PIN diode

BAP1321-04

FEATURES

- High voltage, current controlled
- RF resistor for RF attenuators and switches
- Low diode capacitance
- Low diode forward resistance
- Very low series inductance
- For applications up to 3 GHz.

APPLICATIONS

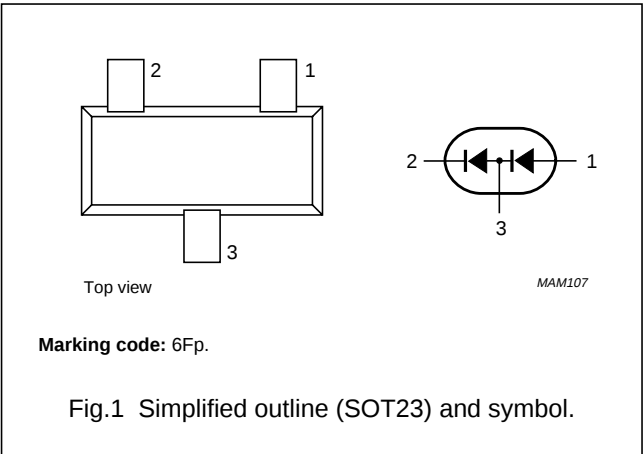
- RF attenuators and switches.

DESCRIPTION

Two planar PIN diodes in series configuration in a SOT23 small SMD plastic package.

PINNING

| PIN | DESCRIPTION       |
|-----|-------------------|
| 1   | anode             |
| 2   | cathode           |
| 3   | common connection |



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL           | PARAMETER                  | CONDITIONS                            | MIN. | MAX. | UNIT               |
|------------------|----------------------------|---------------------------------------|------|------|--------------------|
| <b>Per diode</b> |                            |                                       |      |      |                    |
| $V_R$            | continuous reverse voltage |                                       | –    | 60   | V                  |
| $I_F$            | continuous forward current |                                       | –    | 100  | mA                 |
| $P_{tot}$        | total power dissipation    | $T_s \leq 90\text{ }^{\circ}\text{C}$ | –    | 250  | mW                 |
| $T_{stg}$        | storage temperature        |                                       | –65  | +150 | $^{\circ}\text{C}$ |
| $T_j$            | junction temperature       |                                       | –65  | +150 | $^{\circ}\text{C}$ |

## Silicon PIN diode

## BAP1321-04

**ELECTRICAL CHARACTERISTICS**T<sub>j</sub> = 25 °C unless otherwise specified.

| SYMBOL                         | PARAMETER                | CONDITIONS                                                                                                                       | TYP.  | MAX.  | UNIT |
|--------------------------------|--------------------------|----------------------------------------------------------------------------------------------------------------------------------|-------|-------|------|
| <b>Per diode</b>               |                          |                                                                                                                                  |       |       |      |
| V <sub>F</sub>                 | forward voltage          | I <sub>F</sub> = 50 mA                                                                                                           | 0.95  | 1.1   | V    |
| I <sub>R</sub>                 | reverse leakage current  | V <sub>R</sub> = 60 V                                                                                                            | –     | 100   | nA   |
| C <sub>d</sub>                 | diode capacitance        | V <sub>R</sub> = 0; f = 1 MHz                                                                                                    | 0.42  | –     | pF   |
|                                |                          | V <sub>R</sub> = 1 V; f = 1 MHz                                                                                                  | 0.375 | 0.45  | pF   |
|                                |                          | V <sub>R</sub> = 20 V; f = 1 MHz                                                                                                 | 0.275 | 0.325 | pF   |
| r <sub>D</sub>                 | diode forward resistance | f = 100 MHz; note 1                                                                                                              |       |       |      |
|                                |                          | I <sub>F</sub> = 0.5 mA                                                                                                          | 3.4   | 5.0   | Ω    |
|                                |                          | I <sub>F</sub> = 1 mA                                                                                                            | 2.4   | 3.6   | Ω    |
|                                |                          | I <sub>F</sub> = 10 mA                                                                                                           | 1.2   | 1.8   | Ω    |
| S <sub>21</sub>   <sup>2</sup> | isolation                | I <sub>F</sub> = 100 mA                                                                                                          | 0.85  | 1.3   | Ω    |
|                                |                          | V <sub>R</sub> = 0; f = 900 MHz                                                                                                  | 15.7  | –     | dB   |
|                                |                          | V <sub>R</sub> = 0; f = 1800 MHz                                                                                                 | 10.5  | –     | dB   |
| S <sub>21</sub>   <sup>2</sup> | insertion loss           | V <sub>R</sub> = 0; f = 2450 MHz                                                                                                 | 7.9   | –     | dB   |
|                                |                          | I <sub>F</sub> = 0.5 mA; f = 900 MHz                                                                                             | 0.27  | –     | dB   |
|                                |                          | I <sub>F</sub> = 0.5 mA; f = 1800 MHz                                                                                            | 0.35  | –     | dB   |
| S <sub>21</sub>   <sup>2</sup> | insertion loss           | I <sub>F</sub> = 0.5 mA; f = 2450 MHz                                                                                            | 0.43  | –     | dB   |
|                                |                          | I <sub>F</sub> = 1 mA; f = 900 MHz                                                                                               | 0.21  | –     | dB   |
|                                |                          | I <sub>F</sub> = 1 mA; f = 1800 MHz                                                                                              | 0.29  | –     | dB   |
| S <sub>21</sub>   <sup>2</sup> | insertion loss           | I <sub>F</sub> = 1 mA; f = 2450 MHz                                                                                              | 0.37  | –     | dB   |
|                                |                          | I <sub>F</sub> = 10 mA; f = 900 MHz                                                                                              | 0.14  | –     | dB   |
|                                |                          | I <sub>F</sub> = 10 mA; f = 1800 MHz                                                                                             | 0.21  | –     | dB   |
| S <sub>21</sub>   <sup>2</sup> | insertion loss           | I <sub>F</sub> = 10 mA; f = 2450 MHz                                                                                             | 0.29  | –     | dB   |
|                                |                          | I <sub>F</sub> = 100 mA; f = 900 MHz                                                                                             | 0.10  | –     | dB   |
|                                |                          | I <sub>F</sub> = 100 mA; f = 1800 MHz                                                                                            | 0.18  | –     | dB   |
|                                |                          | I <sub>F</sub> = 100 mA; f = 2450 MHz                                                                                            | 0.26  | –     | dB   |
| τ <sub>L</sub>                 | charge carrier life time | when switched from I <sub>F</sub> = 10 mA to I <sub>R</sub> = 6 mA;<br>R <sub>L</sub> = 100 Ω; measured at I <sub>R</sub> = 3 mA | 0.5   | –     | μs   |
| L <sub>S</sub>                 | series inductance        | I <sub>F</sub> = 100 mA; f = 100 MHz                                                                                             | 1.4   | –     | nH   |

**Note**

1. Guaranteed on AQL basis: inspection level S4, AQL 1.0.

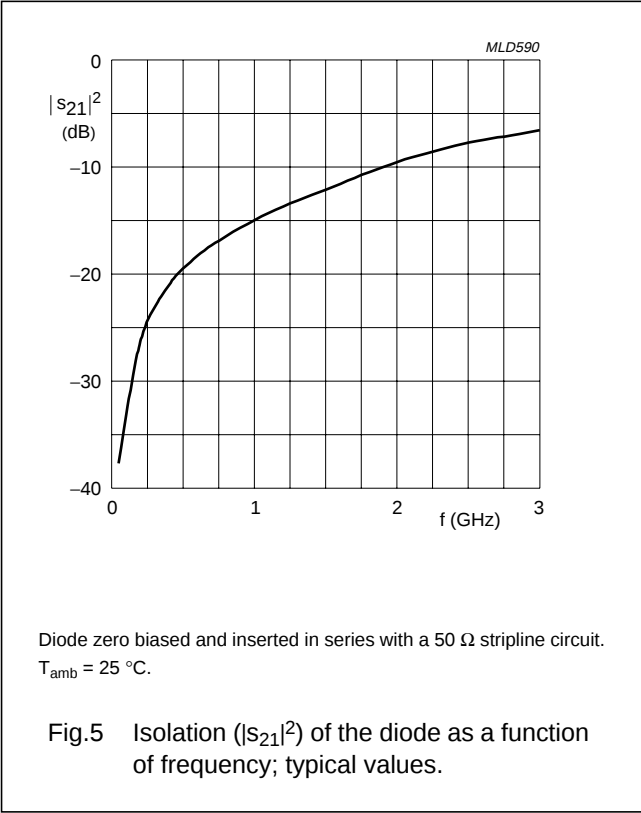
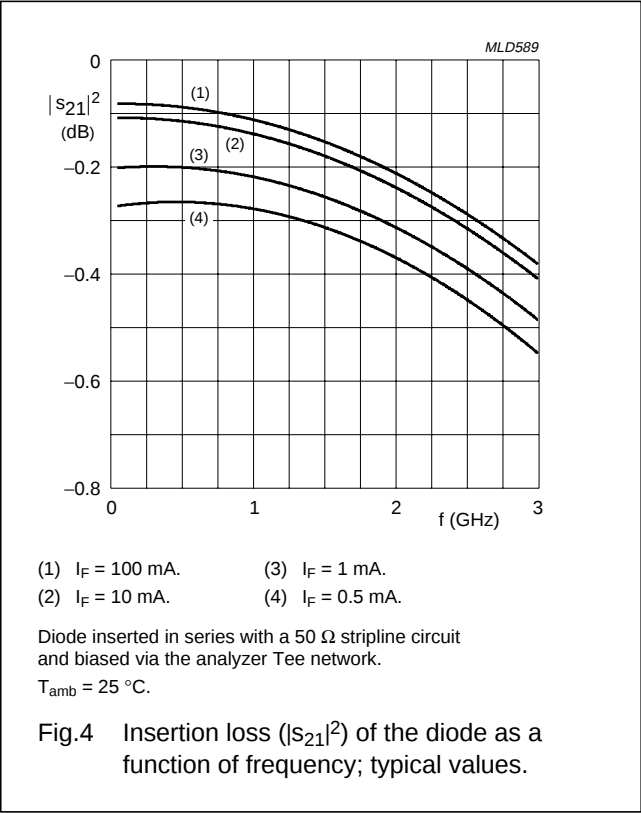
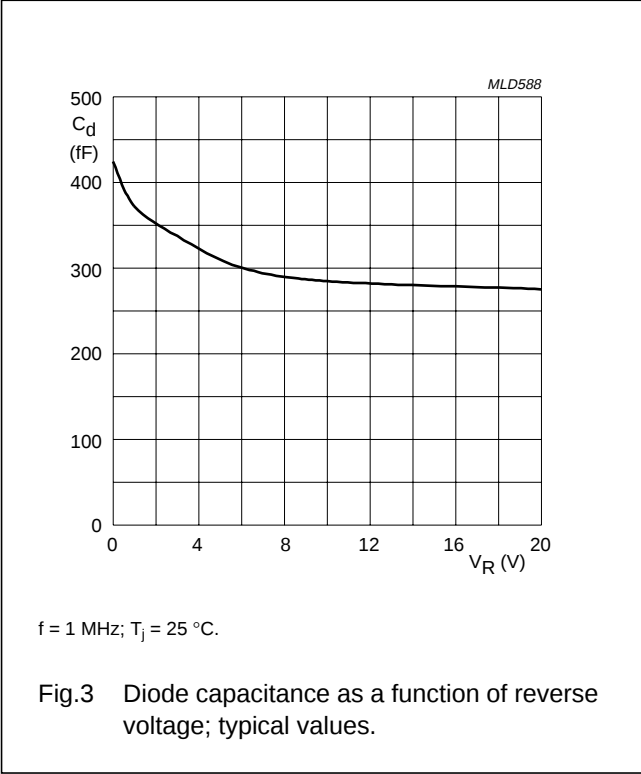
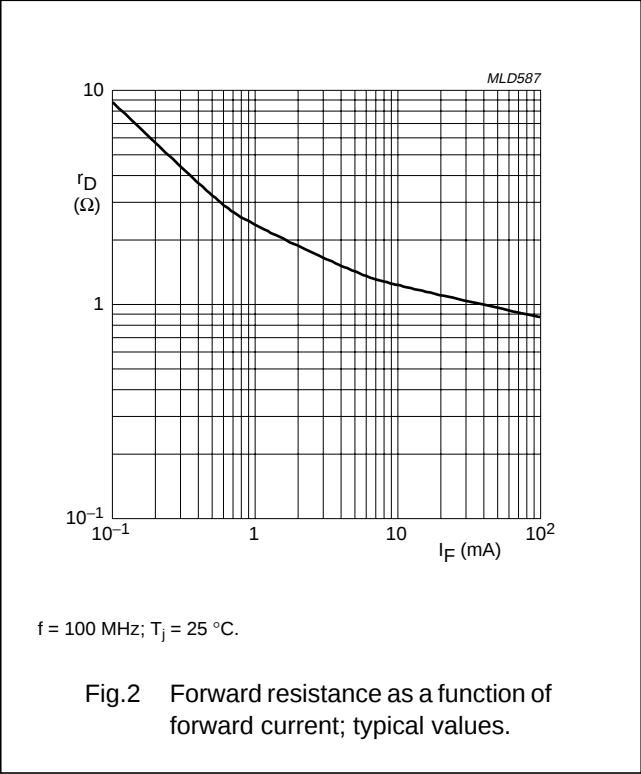
**THERMAL CHARACTERISTICS**

| SYMBOL              | PARAMETER                                           | VALUE | UNIT |
|---------------------|-----------------------------------------------------|-------|------|
| R <sub>th j-s</sub> | thermal resistance from junction to soldering point | 220   | K/W  |

Silicon PIN diode

BAP1321-04

GRAPHICAL DATA



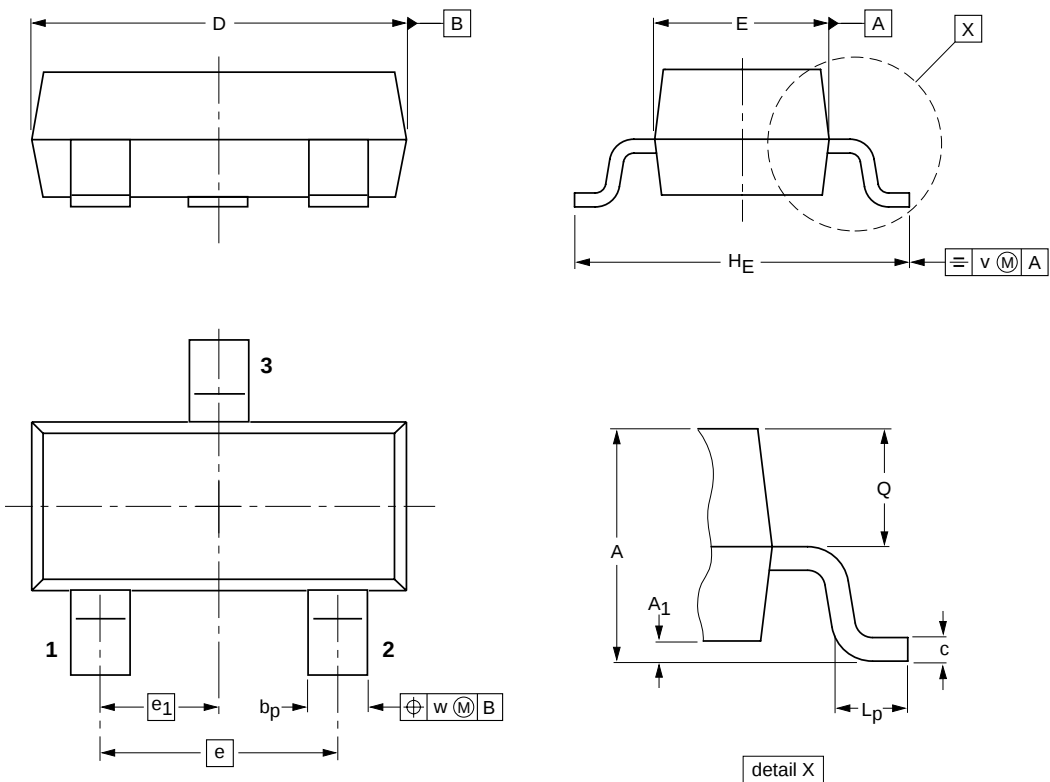
Silicon PIN diode

BAP1321-04

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

| UNIT | A          | A <sub>1</sub> max. | b <sub>p</sub> | c            | D          | E          | e   | e <sub>1</sub> | H <sub>E</sub> | L <sub>p</sub> | Q            | v   | w   |
|------|------------|---------------------|----------------|--------------|------------|------------|-----|----------------|----------------|----------------|--------------|-----|-----|
| mm   | 1.1<br>0.9 | 0.1                 | 0.48<br>0.38   | 0.15<br>0.09 | 3.0<br>2.8 | 1.4<br>1.2 | 1.9 | 0.95           | 2.5<br>2.1     | 0.45<br>0.15   | 0.55<br>0.45 | 0.2 | 0.1 |

| OUTLINE VERSION | REFERENCES |          |      |  | EUROPEAN PROJECTION                                                                   | ISSUE DATE                      |
|-----------------|------------|----------|------|--|---------------------------------------------------------------------------------------|---------------------------------|
|                 | IEC        | JEDEC    | EIAJ |  |                                                                                       |                                 |
| SOT23           |            | TO-236AB |      |  |  | <del>97-02-28</del><br>99-09-13 |

## Silicon PIN diode

BAP1321-04

## DATA SHEET STATUS

| DATA SHEET STATUS <sup>(1)</sup> | PRODUCT STATUS <sup>(2)</sup> | DEFINITIONS                                                                                                                                                                                                                                                                                                            |
|----------------------------------|-------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| Objective data                   | Development                   | This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.                                                                                                                            |
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Silicon PIN diode

BAP1321-04

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